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## Supporting Information - Potassium Doping-induced Variations on Geometric and Photoelectric Properties of MAPbl<sub>3</sub> Perovskite and MAPbl<sub>3</sub>/TiO<sub>2</sub> Junction<sup>†</sup>

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Fig.S 1 Optimized structures of SD-MAPbI<sub>3</sub> slabs: a) two  $K^+$  located well separately (isolated), b) common-vertexed (vertical), c) common-edged (coplanar) and d) directly face-to-face adjacent

 $\textbf{Table 1} \text{ Band gaps and conduction band offsets (in eV) for bulk MAPbI_3, TiO_2 and the junction with K^+ doped inside perovskite layers$ 

Dopants	E <sub>cb,don</sub> .	E <sub>cb,acc</sub> .	$\Delta V_{mix}$	$E_{cb}$ - $V_{don.}$	E <sub>cb</sub> -V <sub>acc</sub> .	Band Offset
Inside K <sup>+</sup>	0.932	0.763	8.096	11.621	19.476	0.242



Fig.S 2 Optimized structures of ID-MAPbl<sub>3</sub> slabs: a) two  $K^+$  located well separately (isolated), b) common-vertexed (vertical), c) common-edged (coplanar) and d) directly face-to-face adjacent



**Fig.S** 3 The *a*) topological structure and its *b*) three views that make two K<sup>+</sup> doped Pb-I cube neither adjacent directly nor coplanar.



Fig.S 4 Schematic diagram of  $MAPbl_3/TiO_2$  heterojunction with different doping manners.



**Fig.S 5** Geometric structure for ID-K<sup>+</sup> set far from MAPbl<sub>3</sub>/TiO<sub>2</sub> junction. The purple arrow represents the direction of movement of K<sup>+</sup> ions during the lattice relaxation.



**Fig.S** 6 Geometric structure for SD-K<sup>+</sup> a) near or b) far from the MAPbl<sub>3</sub>/TiO<sub>2</sub> junction.



**Fig.S** 7 Schematic diagram a) and optimized geometric structure b) of ID-K<sup>+</sup> in PbI<sub>2</sub>-terminated MAPbI<sub>3</sub>/TiO<sub>2</sub> junction.



 $\label{eq:Fig.S} \textbf{8} \ \text{Plane-average potentials of pristine and interstitially doped $MAPbI_3/TiO_2$ heterojunction.}$ 



Fig.S 9 Calculated absorption spectra of  $MAPbI_3/TiO_2$  junction with and without ID-K<sup>+</sup>. The bulk-like  $MAPbI_3$  and anatase  $TiO_2$  are shown for reference.



Fig.S 10 pDOSs of a)pristine TiO<sub>2</sub> and b)trivalent TiO<sub>2</sub><sup>-</sup> by PBE+SOC.



**Fig.S** 11 pDOS for interfacial Ti cations with a) and without b) interfacial ID of K<sup>+</sup> in PbI<sub>2</sub>-terminated MAPbI<sub>3</sub>/TiO<sub>2</sub> junction in PBE+SOC.